

# HYBRID INTEGRATED CIRCUIT MC-9400A

# 320 (240)-BIT AC- PDP DRIVER MODULE

# DESCRIPTION

The MC-9400A is a PDP driver module that incorporates five 64-bit high breakdown voltage output (150 V, 40 mA) CMOS driver ICs. It supports 320 outputs in the case of 4-bit parallel input, and 240 outputs in the case of 3-bit parallel input.

The integrated structure of the MC-9400A, which combines a COB with an aluminum heat sink and an output flexible printed circuit (FPC) board, enables the easy implementation of heat dissipation measures and high-density mounting.

# FEATURES

- Incorporates five  $\mu$ PD16337s with four 16-bit bi-directional shift registers
- Low thermal resistance realized by chip-on-metal structure
- Provided with connector and capacitor for easy mounting on a panel
- Supports output electrode with a narrow pitch through use of a flexible printed circuit board
- Polarity of all driver outputs can be inverted through use of /PC pins
- Supports custom modules

Remark /XXX indicates active low.

## **ORDERING INFORMATION**

Part Number

MC-9400A

Package COB

The information in this document is subject to change without notice.

# **BLOCK DIAGRAM (1/5 CIRCUIT)**



**Remark** Five  $\mu$ PD16337s incorporated : 240 outputs at 3 ch and 320 outputs at 4 ch. See the following block diagram for the  $\mu$ PD16337.

## $\mu$ PD16337 BLOCK DIAGRAM



Note High breakdown voltage CMOS driver 150V, ±40 mA(MAX.).

# \* PIN CONFIGURATION (Top View)



Caution To prevent latch-up breakage, be sure to turn the power on in the order of V<sub>DD1</sub>, logic signal, and V<sub>DD2</sub>, and turn the power off in the reverse order. Keep this order also during a transition period.

# PIN FUNCTIONS

Pin Symbol	Pin Name	Pin No.	I/O	Description
/PC	Polarity inverted	27	CN3	/PC = L : Polarity of all outputs inverted
	input			
BLK	Blanking input	25	CN3	BLK = H : All outputs = H or L
LE	Latch enable input	31	CN3	Automatically latches by a high level input at the rising edge of the
				clock
A11 to A14,	RIGHT data input	1 to 4	CN3	When R,/L = H
A21 to A24,		9 to 12		A11 to A14, A21 to A24, A31 to A34, A41 to A44, A51 to A54: Input
A31 to A34,		17 to 20		B11 to B14, B21 to B24, B31 to B34, B41 to B44, B51 to B54: Output
A41 to A44,		35 to 38		When R,/L = L
A51 to A54		46		A11 to A14, A21 to A24, A31 to A34, A41 to A44, A51 to A54 : Output
But to Bu	LEET data input	5 to 8	CN3	B11 to B14, B21 to B24, B31 to B34, B41 to B44, B51 to B54 : Input
B <sub>24</sub> to B <sub>24</sub>		13 to 16	CNU	
B <sub>21</sub> to B <sub>24</sub> ,		21 to 24		
B <sub>41</sub> to B <sub>44</sub> .		39 to 42		
B <sub>51</sub> to B <sub>54</sub>		47 to 50		
/CLK	Clock input	33	CN3	Executes a shift at the rising edge
R,/L	Shift control input	29	CN3	
, ,				Right Shift mode by T
				$D(1, A) \rightarrow D^{-}(D(2, D(3, a)) \rightarrow D^{-}(D(2, D(3, a)))$
				$SR_1 : B_1 \rightarrow SR_1 = S_1 \rightarrow A_1$ (SR <sub>2</sub> SR <sub>3</sub> and SR <sub>4</sub> also same direction)
O1 to O320	High breakdown	1 to 320	FPC	150 V, 40mA (MAX.)
	voltage output			
Vdd1	Logic block power	1	CN1	5 V ± 10 %
	supply		CN2	
Vdd2	Driver block power	3	CN1	30 V to 130 V
	supply		CN2	
GND	Ground	2	CN1	Connected to system ground
			CN2	
		26,28,	CN3	
		30,32,		
		34		

# **TRUTH TABLE**

#### 1. Shift register block

In	put	Ou	itput	Chiff register	
R,/L	/CLK	А	В	Shift register	
Н	$\downarrow$	logut	Output <sup>Note1</sup>	Execution of right shift	
Н	х	input	Output	Retain	
L	$\downarrow$	Output Note2	lanut	Execution of left shift	
L	Х	Output	input	Retain	

Notes 1. On a clock rise, the data S<sub>57</sub>, S<sub>58</sub>, S<sub>59</sub>, and S<sub>60</sub> are shifted to S<sub>61</sub>, S<sub>62</sub>, S<sub>63</sub>, and S<sub>64</sub>, and output from B<sub>1</sub>, B<sub>2</sub>, B<sub>3</sub>, and B<sub>4</sub>, respectively.

2. On a clock fall, the data S<sub>5</sub>, S<sub>6</sub>, S<sub>7</sub>, and S<sub>8</sub> are shifted to S<sub>1</sub>, S<sub>2</sub>, S<sub>3</sub>, and S<sub>4</sub>, and output from A<sub>1</sub>, A<sub>2</sub>, A<sub>3</sub>, and A<sub>4</sub>, respectively.

Remark X= H or L, H= High level, L= Low level

#### 2. Latch block

LE	/CLK	Output state of latch block (/Ln)			
	$\downarrow$	Latches the data of Sn and retains the output data			
Н	$\downarrow$	Retains the latch data			
L	х	Retains the latch data			

**Remark** X= H or L, H= High level, L= Low level

#### 3. Driver block

/Ln	BLK	/PC	Driver output state
Х	Н	н	H (all driver outputs : H)
х	Н	L	L (all driver outputs : L)
Х	L	Н	Outputs latch data (/Ln)
Х	L	L	Outputs latch data (/Ln) with polarity inverted

Remark X= H or L, H= High level, L= Low level

# **ELECTRICAL CHARACTERISTICS**

#### Absolute maximum ratings (T<sub>A</sub> = +25°C, Vss<sub>1</sub> = Vss<sub>2</sub> = 0 V)

Parameter	Symbol	Ratings	Unit
Logic block supply voltage	VDD1	– 0.5 to + 7.0	V
Driver block supply voltage	VDD2	– 0.5 to + 150	V
Logic block input voltage	V1	– 0.5 to VDD1 + 0.5	V
Driver block output current	lo2	40	mA
Module allowable power dissipation	Рамах.	6 <sup>Note</sup>	W
Junction temperature	Тјмах.	125	°C
Operating ambient temperature	TA	– 10 to + 70	°C
Storage temperature	Tstg	– 40 to + 85	°C

Note The value when mounting this driver module on the aluminum frame by screw.

Caution If the absolute maximum rating of even one of the above parameters is exceeded even momentarily, the quality of the product may be degraded. Absolute maximum ratings, therefore,specify the values exceeding which the product may be physically damaged. Be sure to use the product within the range of the absolute maximum ratings.

Parameter	Symbol	MIN.	TYP.	MAX.	Unit				
Logic block supply voltage	VDD1	4.5	5.0	5.5	V				
Driver block supply voltage	VDD2	30		130	V				
Input voltage high	Vih	0.7 Vdd1		Vdd1	V				
Input voltage low	VIL	0		0.2 VDD1	V				
Driver output current	Іон2	-30			mA				
	IOL2			+30	mA				

Recommended operating range ( $T_A = -10$  to + 70°C, Vss<sub>1</sub> = Vss<sub>2</sub> = 0 V)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Output voltage high	Voh21	VDD2 = 130 V,I	123			V	
Output voltage high	Voh22	VDD2 = 130 V,I	он <b>= –30 mA</b>	110			V
Output voltage low	VOL21	VDD2 = 130 V,I	он <b>= 10 mA</b>			5.0	V
Output voltage low	Vol22	VDD2 = 130 V,I	он = 30 mA			15.0	V
Input leakage current (H1) PU	ILIH1	VDD1 = 7.0 V,V	<sup>2</sup> DD2 = 30 V	-4.0		+4.0	μA
Input leakage current (H2) PC	ILIH2	VDD1 = 7.0 V,V	′DD2 = 30 V	-4.0		+4.0	μA
Input leakage current (L2) PC	ILIL2	VDD1 = 7.0 V,V	<sup>2</sup> DD2 = 30 V	-4.0		+4.0	μA
Input voltage high	Vін	Vdd1 = 5.0 V, Vdd2 = 30 V		3.5			V
Input voltage low	VIL	VDD1 = 5.0 V,V	<sup>′</sup> DD2 = 30 V			1.0	V
Power supply current 1(Logic)	IDD1 a1	V <sub>DD1</sub> = 7.0 V				8	mA
Power supply current 1(Logic)	Idd1 –1		In : High Level			80	μΑ
Power supply current 2	IDD2	VDD1 = 5.0 V	Out : ALL Low			500	μA
(Driver)		VDD2=135 V					
Power supply current 2	IDD2		Out : ALL High			500	μA
(Driver)							
Power supply current 2	IDD2		Out :HLHLLHLH			500	μA
(Driver)							
Power supply current 2	IDD2		Out :LHLHHLHL			500	μA
(Driver)							

## Electrical specifications (TA = +25°C, VSS1 = VSS2 = 0 V)

#### Switching characteristics (T<sub>A</sub> = +25°C, Vss1 = Vss2 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Propagation delay time	tPLH2	Vdd1 = 5.0 V, Vdd2 = 130 V			187.5	ns
Propagation delay time	tPHL2	Vdd1 = 5.0 V, Vdd2 = 130 V			187.5	ns
Propagation delay time	<b>t</b> PLH3	$V_{DD1} = 5.0 \text{ V}, V_{DD2} = 130 \text{ V},$			172.5	ns
		BLK→OUT				
Propagation delay time	<b>t</b> PHL3	$V_{DD1} = 5.0 \text{ V}, V_{DD2} = 130 \text{ V},$			172.5	ns
		BLK→OUT				
Propagation delay time	tPLH4	$V_{DD1} = 5.0 \text{ V}, \text{ V}_{DD2} = 130 \text{ V},$			160.0	ns
		PC→OUT				
Propagation delay time	tPHL4	$V_{DD1} = 5.0 \text{ V}, V_{DD2} = 130 \text{ V},$			160.0	ns
		PC→OUT				
Rise time	tтıн	$V_{DD1} = 5.0 \text{ V}, \text{ V}_{DD2} = 130 \text{ V}$			200.0	ns
Fall time	tтн∟	$V_{DD1} = 5.0 \text{ V}, V_{DD2} = 130 \text{ V}$			200.0	ns
Maximum clock frequency	<b>f</b> мах.	$V_{DD1} = 4.0 \text{ V}, V_{DD2} = 30 \text{ V}$	25.0			MHz

Parameter	Symbol	Conditions MIN. TYP. MAX.		Unit	
Data setup time 1	tsetup1	$V_{DD1} = 4.5 V, V_{DD2} = 30 V$	31.2		ns
Data setup time 2	tsetup2	$V_{DD1} = 4.5 V, V_{DD2} = 30 V$	12.0		ns
Data hold time	<b>t</b> HOLD	$V_{DD1} = 4.5 V, V_{DD2} = 30 V$	8.5		ns
Latch enable time 1	tLE1	$V_{DD1} = 4.5 V, V_{DD2} = 30 V$	27.5		ns
Latch enable time 2	tLE2	$V_{DD1} = 4.5 V, V_{DD2} = 30 V$	17.5		ns
Latch enable time 3	tLE3	V <sub>DD1</sub> = 4.5 V, V <sub>DD2</sub> = 30 V	27.5		ns
Latch enable time 4	tLE4	$V_{DD1} = 4.5 V, V_{DD2} = 30 V$	17.5		ns

# Timing requirements (T<sub>A</sub> = +25°C, V<sub>SS1</sub> = V<sub>SS2</sub> = 0 V)

Timing chart (Right shift)



**Remark** () applies when  $R_{,/L} = L$ 

#### Switching characteristics waveform

#### Propagation delay time

tphl2, tplh2



## Propagation delay time (BLK $\rightarrow$ OUT)

tphl3, tplh3



## Propagation delay time (/PC $\rightarrow$ OUT)

## tphl4, tplh4



#### Rise time, Fall time

tтlн, tтнl



# Maximum clock frequency

**F**MAX.



#### Data setup time1, 2, and Data hold time

tSETUP1, tSETUP2, tHOLD



## Latch enable time1, 2, 3, 4

tle1, tle2, tle3, tle4



## PACKAGE DRAWING (unit : mm)

COB with radiation board attached + FPC module



[MEMO]

# NOTES FOR CMOS DEVICES-

# **1** PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

# **(2)** HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

# **③** STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function. No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

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Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.